Product data sheet

1. General description

High voltage, high speed, planar passivated NPN power switching transistor in a SOT54 (TO-92) plastic package.

2. Features and benefits

- Fast switching
- High typical DC current gain
- High voltage capability of 700 V
- Very low switching and conduction losses

3. Applications

- Compact fluorescent lamps (CFL)
- Low power electronic lighting ballasts
- Off-line self-oscillating power supplies (SOPS) for battery charging

4. Quick reference data

Table 1. Quick reference data

Symbol	Parameter	Conditions		Min	Тур	Max	Unit
I _C	collector current	DC		-	-	1.5	Α
P _{tot}	total power dissipation	T _{lead} ≤ 25 °C; <u>Fig. 1</u>		-	-	2.1	W
V _{CESM}	collector-emitter peak voltage	V _{BE} = 0 V		-	-	700	V
Static characteristics							
h _{FE}	DC current gain	I_C = 0.5 A; V_{CE} = 2 V; T_{lead} = 25 °C		8	17	25	





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5. Pinning information

Table 2. Pinning information

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	В	base		C
2	С	collector		В
3	Е	emitter		, h
			321	E sym123
			TO-92 (SOT54)	

6. Ordering information

Table 3. Ordering information

Type number	Package						
	Name	Description	Version				
PHE13003C	TO-92	plastic single-ended leaded (through hole) package; 3 leads	SOT54				

7. Limiting values

Table 4. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Min	Max	Unit
V _{CESM}	collector-emitter peak voltage	V _{BE} = 0 V	-	700	V
V _{CBO}	collector-base voltage	I _E = 0 A	-	700	V
V _{CEO}	collector-emitter voltage	I _B = 0 A	-	400	V
I _C	collector current	DC	-	1.5	Α
I _{CM}	peak collector current		-	3	Α
I _B	base current	DC	-	0.75	Α
I _{BM}	peak base current		-	1.5	Α
P _{tot}	total power dissipation	T _{lead} ≤ 25 °C; <u>Fig. 1</u>	-	2.1	W
T _{stg}	storage temperature		-65	150	°C
Tj	junction temperature		-	150	°C
V _{EBO}	emitter-base voltage	I _C = 0 A; I(Emitter) = 10 mA	-	9	V

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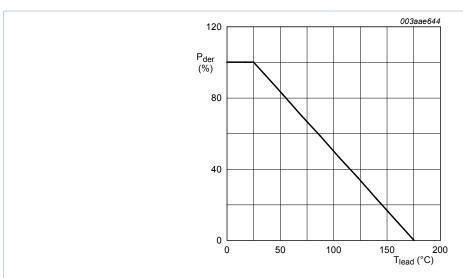


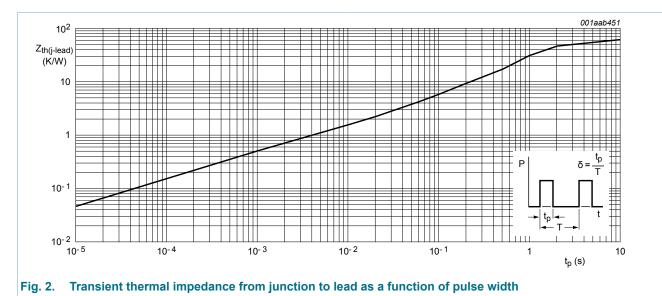
Fig. 1. Normalized total power dissipation as a function of lead temperature

$$P_{der} = \frac{P_{tot}}{P_{tot(25^{\circ}\text{C})}} \times 100 \,\%$$

8. Thermal characteristics

Table 5. Thermal characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
R _{th(j-lead)}	thermal resistance from junction to lead	Fig. 2	-	-	60	K/W
R _{th(j-a)}	thermal resistance from junction to ambient	in free air; printed circuit board mounted; lead length = 4 mm	-	150	-	K/W



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9. Characteristics

Table 6. Characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Dynamic cl	naracteristics					
t _{on}	turn-on time	I _C = 1 A; I _{Bon} = 0.2 A; I _{Boff} = -0.2 A;	-	-	1	μs
t _s storage time	storage time	$R_L = 75 \Omega$; $T_{lead} = 25 ^{\circ}C$; resistive load; Fig. 5; Fig. 6	-	-	4	μs
		I_C = 1 A; I_{Bon} = 0.2 A; V_{BB} = -5 V; L_B = 1 μ H; T_{lead} = 25 °C; inductive load; Fig. 7; Fig. 8	-	0.8	-	μs
t _f	fall time	I_C = 1 A; I_{Bon} = 0.2 A; I_{Boff} = -0.2 A; R_L = 75 Ω ; T_{lead} = 25 °C; resistive load; <u>Fig. 5</u> ; <u>Fig. 6</u>	-	-	0.7	μs
		I_C = 0.5 A; I_{Bon} = 0.1 A; V_{BB} = -5 V; L_B = 1 μ H; T_{lead} = 25 °C; inductive load; Fig. 7; Fig. 8	-	0.1	-	μs
Static char	acteristics					
I _{CES}	collector-emitter cut-off current	V _{BE} = 0 V; V _{CE} = 700 V; T _j = 125 °C	-	-	5	mA
		V _{BE} = 0 V; V _{CE} = 700 V; T _j = 25 °C	-	-	1	mA
I _{CEO}	collector-emitter cut-off current	V _{CE} = 400 V; I _B = 0 A; T _{lead} = 25 °C	-	-	0.1	mA
I _{EBO}	emitter-base cut-off current	V _{EB} = 9 V; I _C = 0 A; T _{lead} = 25 °C	-	-	1	mA
V _{CEOsus}	collector-emitter sustaining voltage	$I_B = 0 \text{ A}; I_C = 1 \text{ mA}; L_C = 25 \text{ mH};$ $T_{lead} = 25 \text{ °C}; \underline{\text{Fig. 3}}; \underline{\text{Fig. 4}}$	400	-	-	V
V _{CEsat}	collector-emitter	I _C = 0.5 A; I _B = 0.1 A; T _{lead} = 25 °C	-	-	0.5	V
	saturation voltage	I _C = 1 A; I _B = 0.25 A; T _{lead} = 25 °C	-	-	1	V
		I _C = 1.5 A; I _B = 0.5 A; T _{lead} = 25 °C	-	-	1.5	V
V _{BEsat}	base-emitter saturation	I _C = 0.5 A; I _B = 0.1 A; T _{lead} = 25 °C	-	-	1	V
	voltage	I _C = 1 A; I _B = 0.25 A; T _{lead} = 25 °C	-	-	1.2	V
h _{FE}	DC current gain	I _C = 0.5 A; V _{CE} = 2 V; T _{lead} = 25 °C	8	17	25	
		I _C = 1 A; V _{CE} = 2 V; T _{lead} = 25 °C	5	9	15	

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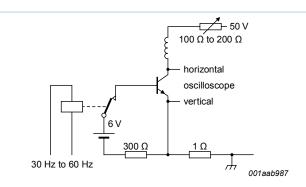


Fig. 3. Test circuit for collector-emitter sustaining voltage

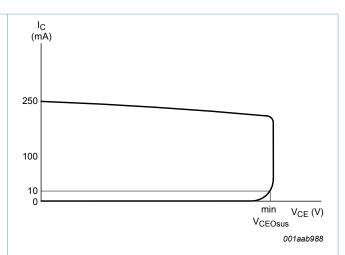


Fig. 4. Oscilloscope display for collector-emitter sustaining voltage test waveform

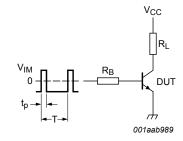


Fig. 5. Test circuit for resistive load switching

 $V_{IM} = -6$ to +8 V; $V_{CC} = 250$ V; $t_p = 20$ μ s; $\delta = \frac{t_p}{T} = 0.01$ R_B and R_L calculated from I_{Con} and I_{Bon} requirements.

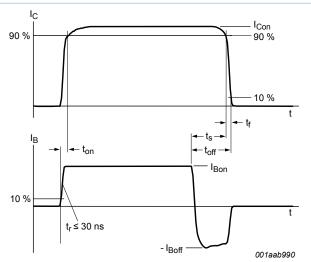


Fig. 6. Switching times waveforms for resistive load

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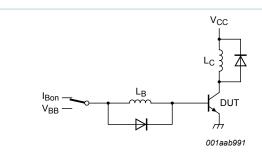


Fig. 7. Test circuit for inductive load switching

$$V_{CC} = 300 \ V; V_{BB} = -5 \ V; L_{C} = 200 \ \mu H; L_{B} = 1 \ \mu H$$

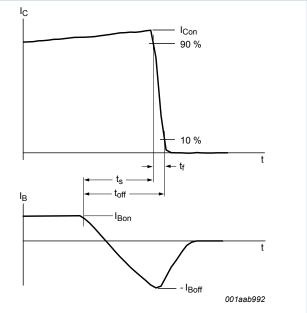


Fig. 8. Switching times waveforms for inductive load

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10. Package outline

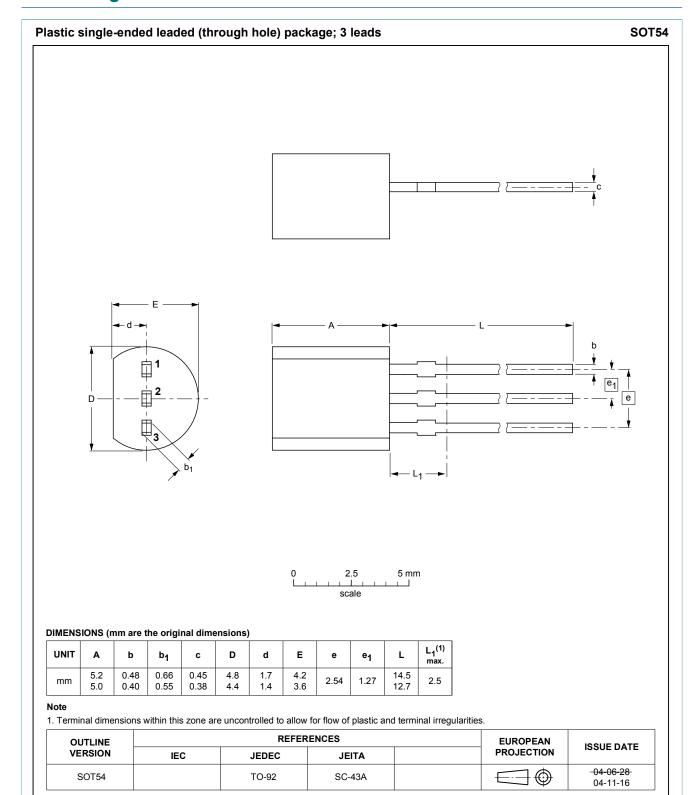


Fig. 9. Package outline TO-92 (SOT54)

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